

Name: \_\_\_\_\_

Student ID #: \_\_\_\_\_

**EECS 170A**  
**Homework #3**

HW will be collected in discussion section.  
Please do not turn your HW in anywhere else.  
Due: 10:50am Thursday, October 20, 2011.

Please *staple* this sheet to the front of your homework.

1	2	3	4	Total
/25	/25	/25	/25	/100

- 1) For Si at room temperature ( $n_i = 10^{10} / \text{cm}^3$ ), Draw the **band diagram** showing ( $E_c$ ,  $E_v$ ,  $E_f$ ,  $E_i$ ) and indicate your findings:
  - a) For  $N_d = 10^{15} / \text{cm}^3$
  - b) For  $N_a = 10^{17} / \text{cm}^3$
- 2) Calculate  $n_i$ ,  $p_i$  for Si:
  - a) When temperature is 0 degree Celcius.
  - b) When temperature is 100 degree Celcius.
- 3) Given a Si semiconductor that has its Fermi level  $0.25E_g$  below the conduction band.
  - a) Find the resistivity in (Ohm-cm)
  - b) Find the electron mobility in ( $\text{cm}^2/\text{V-s}$ )
- 4) Given a n-type semiconductor that has ( $\mu_n$ ) of  $380 \text{cm}^2/\text{V-s}$ 
  - a) Find the resistivity in (Ohm-cm)
  - b) Draw a band diagram (as in Problem #1) and indicate your findings.